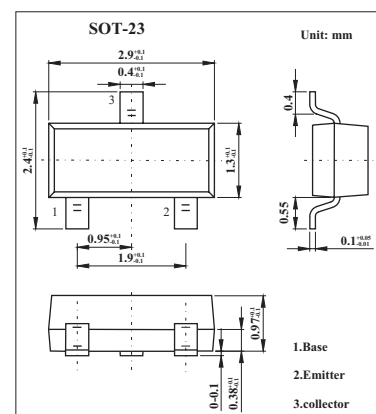


High Voltage Transistor

FMMT597

■ Features

- SOT23 PNP silicon planar

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-300	V
Collector-emitter voltage	V_{CE0}	-300	V
Emitter-base voltage	V_{EB0}	-5	V
Peak collector current	I_{CM}	-1	A
Collector current	I_C	-0.2	A
Base current	I_B	-200	mA
Power dissipation	P_{tot}	500	mW
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

FMMT597

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC=-100μA	-300			V
Collector-emitter breakdown voltage *	V(BR)CEO	IC=-10mA	-300			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100μA	-5			V
Collector cutoff current	ICBO	VCE=-250V			-100	nA
Collector-Emitter Cut-Off Current	ICES	VCE=-250V			-100	nA
Emitter cut-off current	IEBO	VEB=-4V			-100	nA
Collector-emitter saturation voltage *	VCE(sat)	IC=-50mA, IB=-5mA			-0.25	V
		IC=-100mA, IB=-20mA			-0.25	V
Base-emitter saturation voltage *	VBE(sat)	IC=-100mA, IB=-20mA			-1.0	V
Base-emitter voltage *	VBE(ON)	IC=-100mA, VCE=-10V			-0.85	V
Static Forward Current Transfer Ratio	hFE	IC=-1mA, VCE=-10V	100			
		IC=-50mA, VCE=-10V *	100		300	
		IC=-100mA, VCE=-10V *	100			
Current-gain-bandwidth product	fT	IC=-50mA, VCE=-10V, f=100MHz	75			MHz
Output capacitance	Cobo	VCE=-10V, f=1MHz			10	pF

* Pulse test: tp = 300 μs; d ≤ 0.02.

■ Marking

Marking	597
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